

MC74VHC1G125

Product Preview

Noninverting 3-State Buffer

The MC74VHC1G125 is an advanced high speed CMOS noninverting 3-state buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffered 3-state output which provides high noise immunity and stable output.

The MC74VHC1G125 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1G125 to be used to interface 5V circuits to 3V circuits.

- High Speed: $t_{PD} = 3.5\text{ns}$ (Typ) at $V_{CC} = 5\text{V}$
- Low Power Dissipation: $I_{CC} = 2\mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; MM > 200V

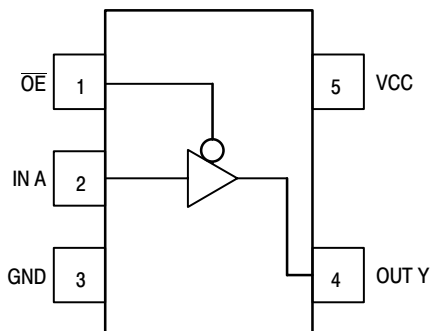


Figure 1. 5-Lead SOT-353 Pinout (Top View)

LOGIC SYMBOL



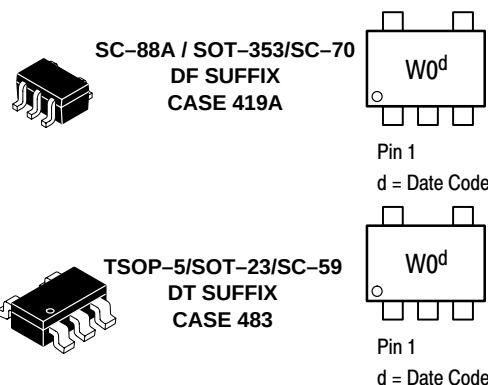
Figure 2. Logic Symbol



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MARKING DIAGRAMS



PIN ASSIGNMENT	
1	$\overline{OE}$
2	IN A
3	GND
4	OUT Y
5	V_{CC}

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

FUNCTION TABLE

A Input	$\overline{OE}$ Input	Y Output
L	L	L
H	L	H
X	H	Z

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

MC74VHC1G125

MAXIMUM RATINGS*

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V_{CC}	-0.5 to +7.0	V
DC Input Voltage	V_{IN}	-0.5 to +7.0	V
DC Output Voltage $V_{CC} = 0$ High or Low State	V_{OUT}	-0.5 to 7.0 -0.5 to $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	-20	mA
Output Diode Current ($V_{OUT} < GND$; $V_{OUT} > V_{CC}$)	I_{OK}	+20	mA
DC Output Current, per Pin	I_{OUT}	+25	mA
DC Supply Current, V_{CC} and GND	I_{CC}	+50	mA
Power dissipation in still air, SC-88A †	P_D	200	mW
Lead temperature, 1 mm from case for 10 s	T_L	260	°C
Storage temperature	T_{stg}	-65 to +150	°C

* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

† Derating — SC-88A Package: -3 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	V_{CC}	2.0	5.5	V
DC Input Voltage	V_{IN}	0.0	5.5	V
DC Output Voltage	V_{OUT}	0.0	V_{CC}	V
Operating Temperature Range	T_A	-55	+125	°C
Input Rise and Fall Time $V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$	t_r, t_f	0 0	100 20	ns/V

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

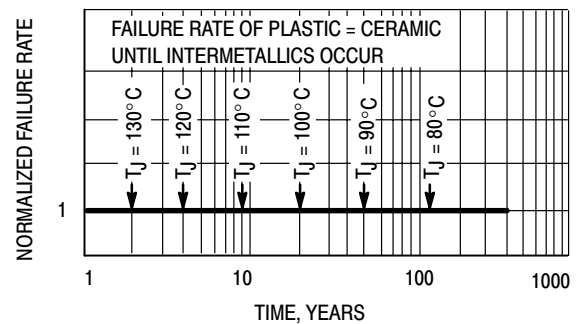


Figure 3. Failure Rate vs. Time Junction Temperature

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -4mA I _{OH} = -8mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OL} = 4mA I _{OL} = 8mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{OZ}	Maximum 3-State Leakage Current	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND	5.5			±0.25		±2.5		±2.5	μA
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			2.0		20		40	μA

AC ELECTRICAL CHARACTERISTICS (C_{load} = 50 pF, Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A ≤ 85°C		T _A ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Y (Figures 3 and 5)	V _{CC} = 3.0 ± 0.3V C _L = 15 pF C _L = 50 pF		4.5 6.4	8.0 11.5		9.5 13.0		12.0 16.0	ns
		V _{CC} = 5.0 ± 0.5V C _L = 15 pF C _L = 50 pF		3.5 4.5	5.5 7.5		6.5 8.5		8.5 10.5	
t _{PZL} , t _{PZH}	Maximum Output Enable Time, Input $\overline{OE}$ to Y (Figures 4 and 5)	V _{CC} = 3.3 ± 0.3V C _L = 15 pF R _L = 1kΩ C _L = 50 pF		4.5 6.4	8.0 11.5		9.5 13.0		11.5 15.0	ns
		V _{CC} = 5.0 ± 0.5V C _L = 15 pF R _L = 1kΩ C _L = 50 pF		3.5 4.5	5.1 7.1		6.0 8.0		8.5 10.5	
t _{PLZ} , t _{PHZ}	Maximum Output Disable Time, Input $\overline{OE}$ to Y (Figures 4 and 5)	V _{CC} = 3.3 ± 0.3V C _L = 15 pF R _L = 1kΩ C _L = 50 pF		6.5 8.0	9.7 13.2		11.5 15.0		14.5 18.0	ns
		V _{CC} = 5.0 ± 0.5V C _L = 15 pF R _L = 1kΩ C _L = 50 pF		4.8 7.0	6.8 8.8		8.0 10.0		10.0 12.0	
C _{IN}	Maximum Input Capacitance			4.0	10		10		10	pF
C _{OUT}	Maximum 3-State Output Capacitance (Output in High Impedance State)			6.0						pF

C _{PD}	Power Dissipation Capacitance (Note 1.)	Typical @ 25°C, V _{CC} = 5.0V	pF
		8.0	

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

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SWITCHING WAVEFORMS

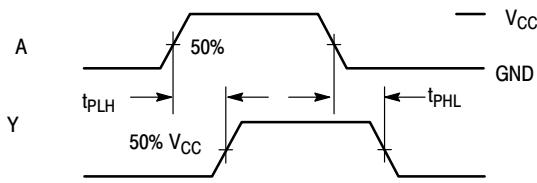


Figure 4.

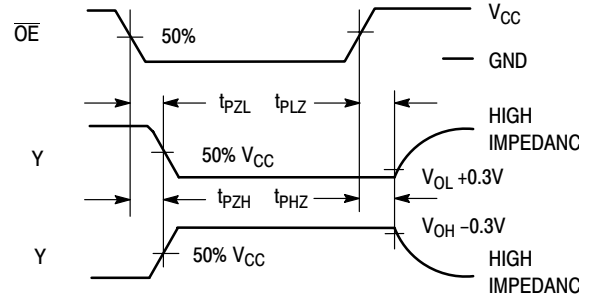
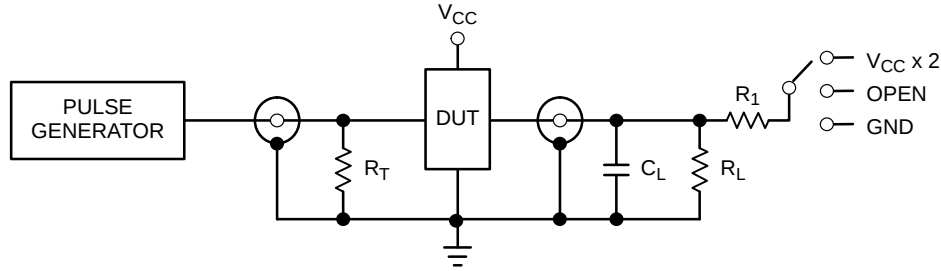


Figure 5.



TEST	SWITCH
t_{PZL}, t_{PLZ}	V_{CC}
t_{PZH}, t_{PHZ}	GND
t_{PLH}, t_{PHL}	OPEN

$C_L = 50$ pF equivalent (Includes jig and probe capacitance) or 15 pF
 $R_L = R_1 = 500 \Omega$ or equivalent
 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 6. Test Circuit

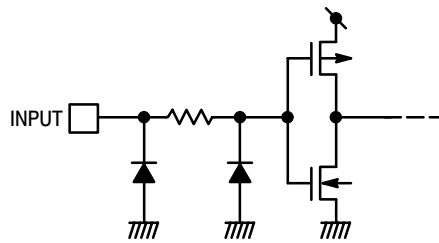


Figure 7. Input Equivalent Circuit

DEVICE ORDERING INFORMATION

Device Order Number	Device Nomenclature						Package Type (Name/SOT#/ Common Name)	Tape and Reel Size
	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix		
MC74VHC1G125DFT2	MC	74	VHC1G	125	DF	T2	SC-88A / SOT-353 / SC-70	178 mm (7") 3000 Unit
MC74VHC1G125DFT4	MC	74	VHC1G	125	DF	T4	SC-88A / SOT-353 / SC-70	330 mm (13") 10000 Unit
MC74VHC1G125DTT1	MC	74	VHC1G	125	DT	T1	TSOPS / SOT-23 / SC-59	178 mm (7") 3000 Unit
MC74VHC1G125DTT3	MC	74	VHC1G	125	DT	T3	TSOPS / SOT-23 / SC-59	330 mm (13") 10000 Unit

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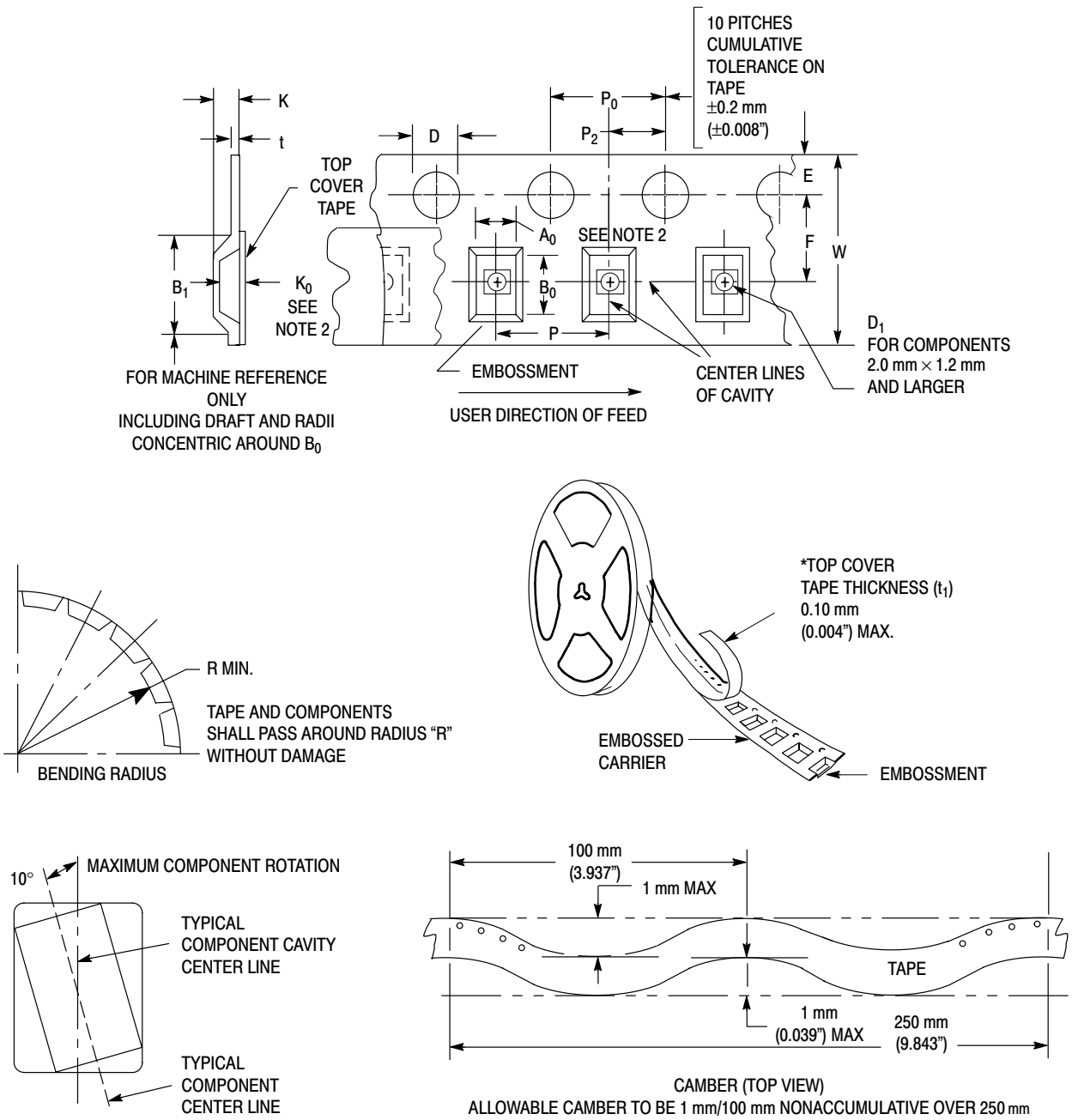


Figure 8. Carrier Tape Specifications

EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

Tape Size	B_1 Max	D	D_1	E	F	K	P	P_0	P_2	R	T	W
8 mm	4.35 mm (0.171")	1.5 +0.1/-0.0 mm (0.059 +0.004/-0.0")	1.0 mm Min (0.039")	1.75 ± 0.1 mm (0.069 ± 0.004 ")	3.5 ± 0.5 mm (1.38 ± 0.002 ")	2.4 mm (0.094")	4.0 ± 0.10 mm (0.157 ± 0.004 ")	4.0 ± 0.1 mm (0.156 ± 0.004 ")	2.0 ± 0.1 mm (0.079 ± 0.002 ")	25 mm (0.98")	0.3 ± 0.05 mm (0.01 +0.0038/-0.0002")	8.0 ± 0.3 mm (0.315 ± 0.012 ")

1. Metric Dimensions Govern—English are in parentheses for reference only.
2. A_0 , B_0 , and K_0 are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

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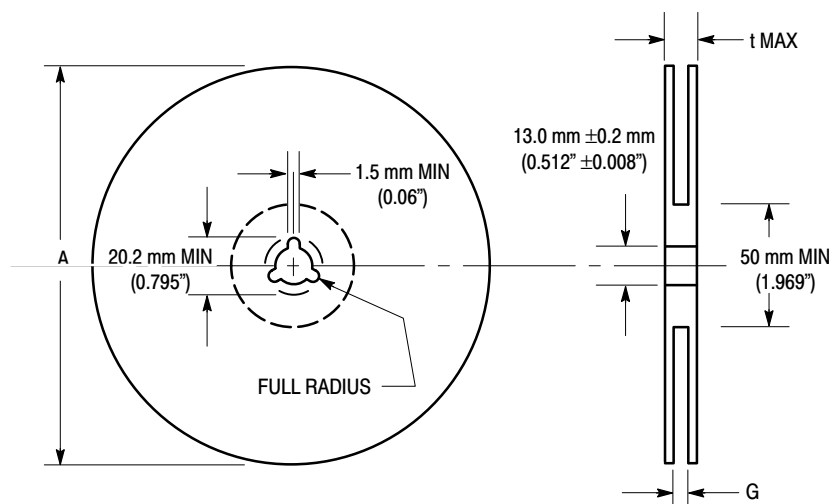


Figure 9. Reel Dimensions

REEL DIMENSIONS

Tape Size	T&R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")
8 mm	T3, T4	330 mm (13")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")

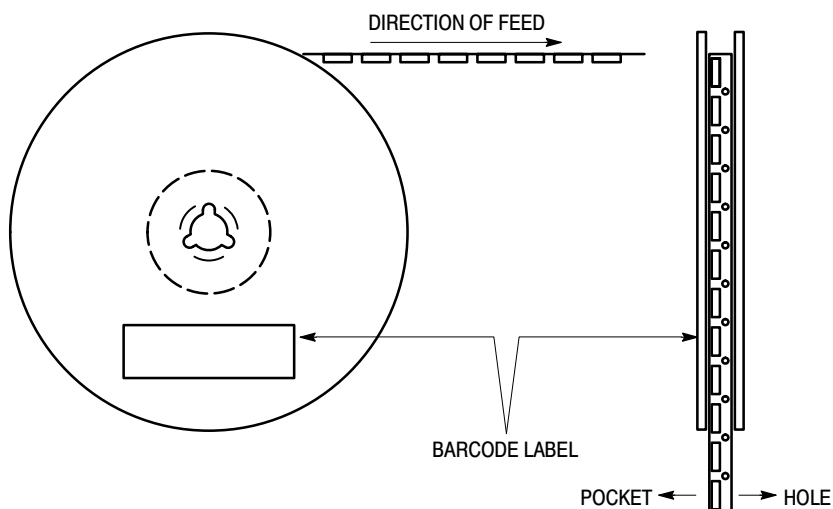


Figure 10. Reel Winding Direction

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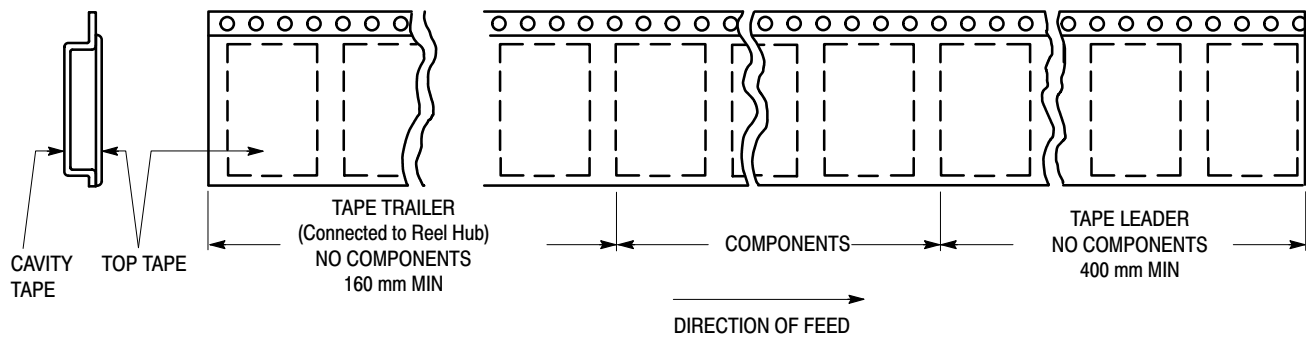


Figure 11. Tape Ends for Finished Goods

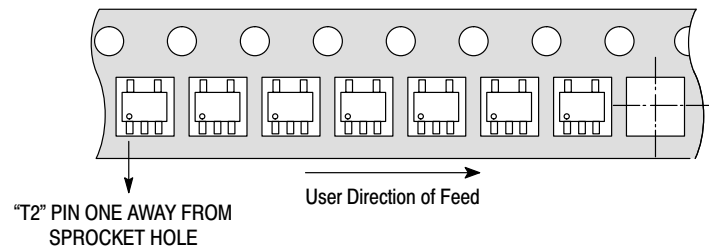


Figure 12. DFT2 and DFT4 (SC88A) Reel Configuration/Orientation

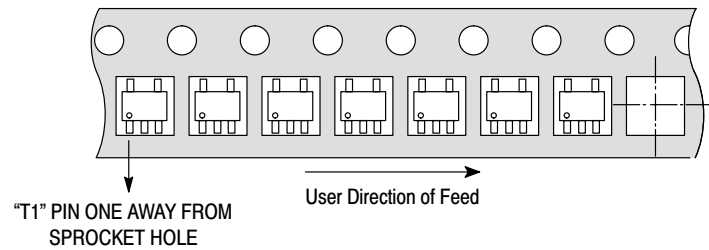
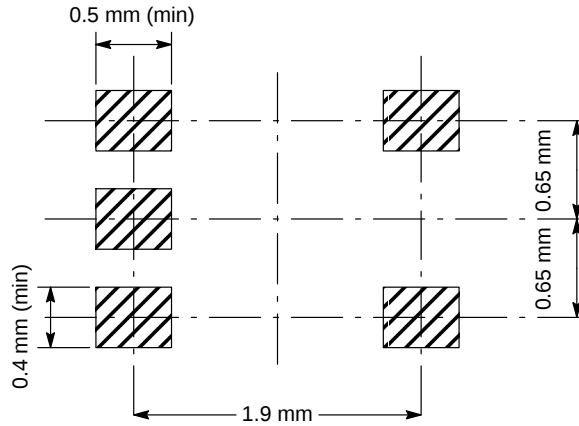
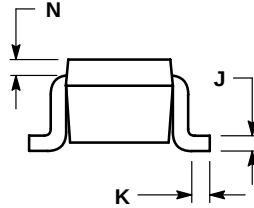
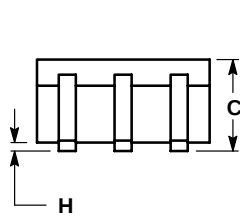
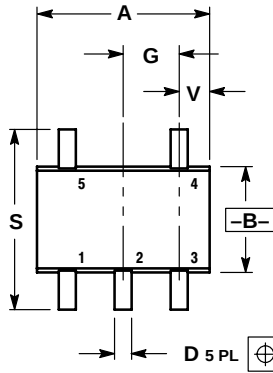


Figure 13. DTT1 and DTT3 (TSOP5) Reel Configuration/Orientation

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PACKAGE DIMENSIONS

SC-88A / SOT-353 / SC-70
DF SUFFIX
5-LEAD PACKAGE
CASE 419A-01
ISSUE B



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20
V	0.012	0.016	0.30	0.40

MC74VHC1G125

PACKAGE DIMENSIONS

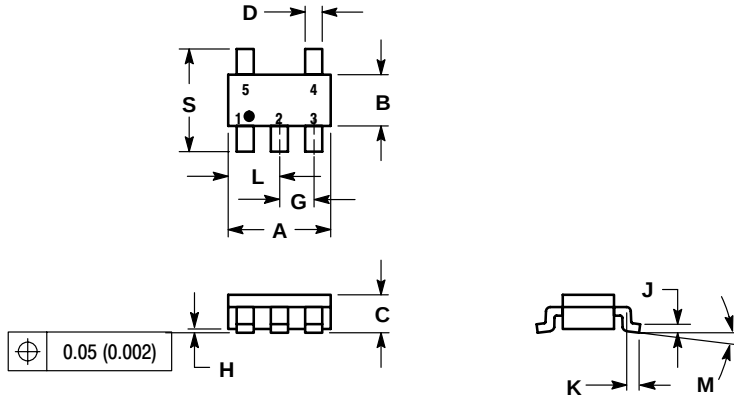
TSOP-5 / SOT-23 / SC-59

DT SUFFIX

5-LEAD PACKAGE

CASE 483-01

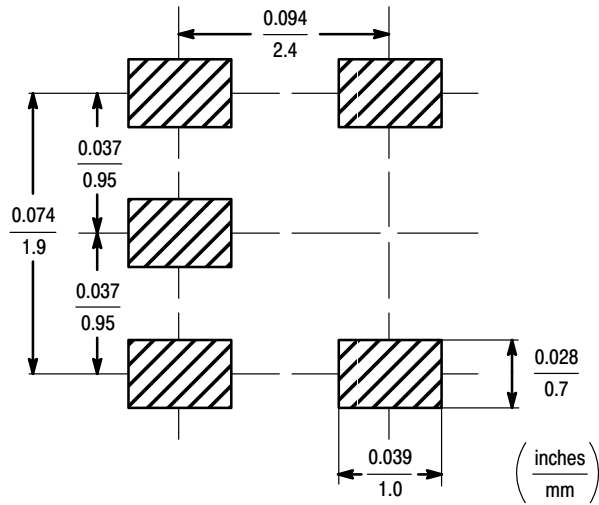
ISSUE A



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.1142	0.1220
B	1.30	1.70	0.0512	0.0669
C	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.00	0.0335	0.0413
H	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
M	0°	10°	0°	10°
S	2.50	3.00	0.0985	0.1181



Notes

Notes

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